1. Scope :

This specification applies to InGaAs PIN photodiode chips.
Device No. ED-MPD90VB

2. Structure :

2-1. Type : PIN diode.
2-2. Electrodes :
Top side (Anode) : Au alloy.
Back side (Cathode) : Au alloy.

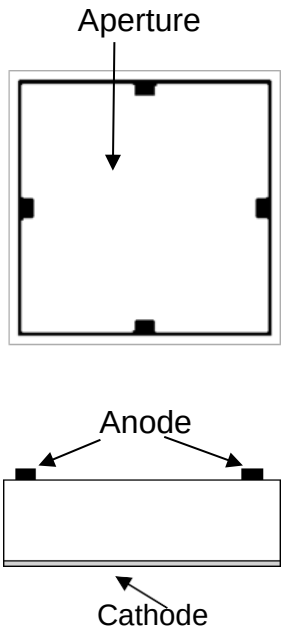
3. Size :

3-1. Chip size : 86.4 mils × 86.4 mils (2.195 mm × 2.195 mm).
3-2. Chip thickness : 11.8 ± 1 mils (0.30 ± 0.025 mm).
3-3. Aperture size : 78.7 mils × 78.7 mils (2.00 mm x 2.00 mm).
3-4. Bonding pad (Anode) : 3.9 x 3.9mils (0.100 mmx 0.100mm).
3-5. Pattern drawing : Refer to the attached drawing.

4. Electro-optical characteristics (Ta = 25 ℃)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
※Reverse Dark Current	I_D	V_R=5V Ee=0mW/cm^2	-	-	5	nA
※Reverse Breakdown Voltage	$V_{(BR)R}$	I_R=1uA Ee=0mW/cm^2	30	-	-	V
※Forward Voltage	V_F	I_F=3mA Ee=0mW/cm^2	-	-	0.7	V
Capacitance	Cp	V_R=5V f=1MHz	170	-	-	pF
Responsivity	Resp	V_R=5V Wavelength =1310nm	0.8	-	-	A/W

※Based on 100% probing



5. Typical Electro-Optical Characteristics Curve:

Fig 1. Relative Responsivity vs Wavelength